MSCSM170HRM451AG

T-Type SiC MOSFET Power Module

Product Overview

The MSCSM170HRM451AG device is a T-type Silicon Carbide (SiC) MOSFET power module with a phase leg 1700V, 64A and a dual common source 1200V, 89A.

The following figures show the electrical and pinout location diagrams of the device.

Figure 1. Electrical Diagram

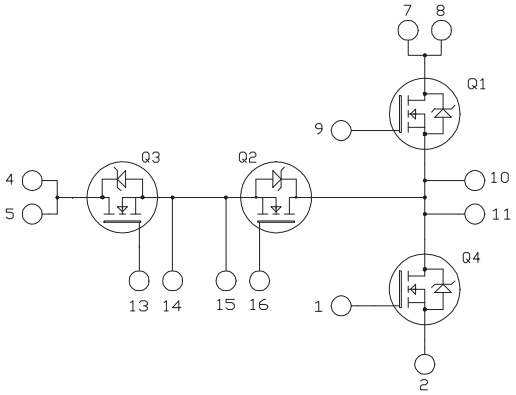
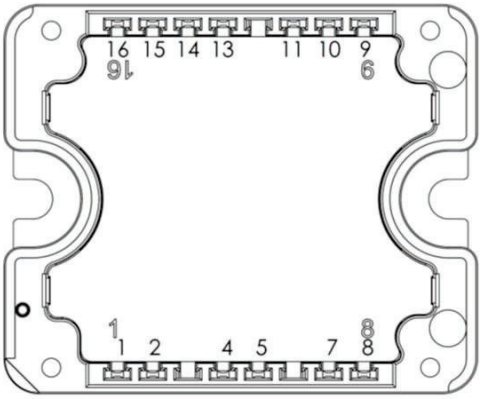


Figure 2. Pinout Location Diagram



Notes:

- Pins 4/5; 10/11; 7/8 must be shorted together.
- All ratings at T_J = 25 °C, unless otherwise specified.

⚠ CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The MSCSM170HRM451AG device has the following features:

- SiC Power MOSFET
  - High speed switching
  - Low $R_{DS(on)}$
  - Ultra low loss
- Very low stray inductance
- AlN substrate for improved thermal performance

Benefits

The MSCSM170HRM451AG device has the following benefits:

- Outstanding performance at high-frequency operation
- High-power and high-efficiency rectifiers and converters
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Applications

The MSCSM170HRM451AG device has the following applications:

- Solar inverter
- Three level inverter
- Uninterruptible power supplies

1. Electrical Specifications

The following sections describe the electrical specifications of the MSCSM170HRM451AG device.

1.1 Q1 and Q4 1700V Phase Leg SiC MOSFETs Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings (per SiC MOSFET) of the Q1 and Q4 1700V phase leg SiC MOSFETs.

Table 1-1. Absolute Maximum Ratings: Q1 and Q4 1700V Phase Leg SiC MOSFETs

Symbol	Parameter		Maximum Ratings	Unit
V_{DSS}	Drain-source voltage		1700	V
I_D	Continuous drain current	T_C = 25 °C	64[1]	A
		T_C = 80 °C	51[1]	
I_{DM}	Pulsed drain current		130	
V_{GS}	Gate-source voltage		−10/23	V
$R_{DS(on)}$	Drain-source ON resistance		45	mΩ
P_D	Power dissipation	T_C = 25 °C	319	W

Note:

1. The specification of the SiC MOSFET device, but output current should be limited due to the size of the power connectors.

The following table lists the electrical characteristics (per SiC MOSFET) of the Q1 and Q4 1700V phase leg SiC MOSFETs.

Table 1-2. Electrical Characteristics: Q1 and Q4 1700V Phase Leg SiC MOSFETs

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0V; V_{DS} = 1700V		—	10	100	µA
$R_{DS(on)}$	Drain-source ON resistance	V_{GS} = 20V I_D = 30A	T_J = 25 °C	—	35	45	mΩ
			T_J = 175 °C	—	62	—	
$V_{GS(th)}$	Gate threshold voltage	V_{GS} = V_{DS}; I_D = 2.5 mA		1.8	3.2	—	V
I_{GSS}	Gate-source leakage current	V_{GS} = 20V; V_{DS} = 0V		—	—	150	nA

The following table lists the dynamic characteristics (per SiC MOSFET) of the Q1 and Q4 1700V phase leg SiC MOSFETs.

Table 1-3. Dynamic Characteristics: Q1 and Q4 1700V Phase Leg SiC MOSFETs

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0V		—	3300	—	pF
C_{oss}	Output capacitance	V_{DS} = 1000V		—	150	—	
C_{rss}	Reverse transfer capacitance	f = 1 MHz		—	10	—	
Q_g	Total gate charge	V_{GS} = −5V/20V		—	178	—	nC
Q_{gs}	Gate-source charge	V_{Bus} = 850V		—	49	—	
Q_{gd}	Gate-drain charge	I_D = 30A		—	27	—	
$T_{d(on)}$	Turn-on delay time	V_{GS} = −5V/20V	T_J = 150 °C	—	19	—	ns
T_r	Rise time	V_{Bus} = 900V		—	23	—	
$T_{d(off)}$	Turn-off delay time	I_D = 50A		—	30	—	
T_f	Fall time	R_{GON} = 4.7Ω R_{GOFF} = 2.7Ω		—	15	—	
E_{on}	Turn-on energy	V_{GS} = −5V/20V	T_J = 150 °C	—	1.7	—	mJ
E_{off}	Turn-off energy	V_{Bus} = 900V I_D = 50A R_{GON} = 4.7Ω R_{GOFF} = 2.7Ω		—	0.09	—	
R_{Gint}	Internal gate resistance			—	0.85	—	Ω
R_{thJC}	Junction-to-case thermal resistance			—	—	0.47	°C/W

The following table lists the body diode ratings and characteristics (per SiC MOSFET) of the Q1 and Q4 1700V phase leg SiC MOSFETs.

Table 1-4. Body Diode Ratings and Characteristics: Q1 and Q4 1700V Phase Leg SiC MOSFETs

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	V_{GS} = 0V; I_{SD} = 30A	—	3.7	—	V
		V_{GS} = −5V; I_{SD} = 30A	—	3.9	—	
t_{rr}	Reverse recovery time	I_{SD} = 30A	—	27	—	ns
Q_{rr}	Reverse recovery charge	V_{GS} = −5V	—	650	—	nC
I_{rr}	Reverse recovery current	V_R = 900V di_F/dt = 1000 A/µs	—	46	—	A

1.2 Q2 and Q3 1200V Dual Common Source SiC MOSFETs Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings (per SiC MOSFET) of the Q2 and Q3 1200V dual common source SiC MOSFETs.

Table 1-5. Absolute Maximum Ratings: Q2 and Q3 1200V Dual Common Source SiC MOSFETs

Symbol	Parameter		Maximum Ratings	Unit
V_{DSS}	Drain-source voltage		1200	V
I_D	Continuous drain current	T_C = 25 °C	89[1]	A
		T_C = 80 °C	71[1]	
I_{DM}	Pulsed drain current		180	
V_{GS}	Gate-source voltage		−10/23	V
$R_{DS(on)}$	Drain-source ON resistance		31	mΩ
P_D	Power dissipation	T_C = 25 °C	395	W

Note:

1. The specification of the SiC MOSFET device, but output current should be limited due to the size of the power connectors.

The following table lists the electrical characteristics (per SiC MOSFET) of the Q2 and Q3 1200V dual common source SiC MOSFETs.

Table 1-6. Electrical Characteristics: Q2 and Q3 1200V Dual Common Source SiC MOSFETs

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0V; V_{DS} = 1200V		—	10	100	µA
$R_{DS(on)}$	Drain-source ON resistance	V_{GS} = 20V I_D = 40A	T_J = 25 °C	—	25	31	mΩ
			T_J = 175 °C	—	40	—	
$V_{GS(th)}$	Gate threshold voltage	V_{GS} = V_{DS}; I_D = 3 mA		1.8	2.8	—	V
I_{GSS}	Gate-source leakage current	V_{GS} = 20V; V_{DS} = 0V		—	—	150	nA

The following table lists the dynamic characteristics (per SiC MOSFET) of the Q2 and Q3 1200V dual common source SiC MOSFETs.

Table 1-7. Dynamic Characteristics: Q2 and Q3 1200V Dual Common Source SiC MOSFETs

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0V		—	3020	—	pF
C_{oss}	Output capacitance	V_{DS} = 1000V		—	270	—	
C_{rss}	Reverse transfer capacitance	f = 1 MHz		—	25	—	
Q_g	Total gate charge	V_{GS} = −5V/20V		—	232	—	nC
Q_{gs}	Gate-source charge	V_{Bus} = 800V		—	41	—	
Q_{gd}	Gate-drain charge	I_D = 40A		—	50	—	
$T_{d(on)}$	Turn-on delay time	V_{GS} = −5V/20V	T_J = 150 °C	—	30	—	ns
T_r	Rise time	V_{Bus} = 800V		—	30	—	
$T_{d(off)}$	Turn-off delay time	I_D = 50A		—	50	—	
T_f	Fall time	R_{GON} = 8Ω R_{GOFF} = 4.7Ω		—	25	—	
E_{on}	Turn-on energy	V_{GS} = −5V/20V	T_J = 150 °C	—	1.2	—	mJ
E_{off}	Turn-off energy	V_{Bus} = 600V I_D = 50A R_{GON} = 8Ω R_{GOFF} = 4.7Ω		—	0.66	—	
R_{Gint}	Internal gate resistance			—	0.88	—	Ω
R_{thJC}	Junction-to-case thermal resistance			—	—	0.38	°C/W

The following table lists the body diode ratings and characteristics (per SiC MOSFET) of the Q2 and Q3 1200V dual common source SiC MOSFETs.

Table 1-8. Body Diode Ratings and Characteristics: Q2 and Q3 1200V Dual Common Source SiC MOSFETs

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	V_{GS} = 0V; I_{SD} = 40A	—	4	—	V
		V_{GS} = −5V; I_{SD} = 40A	—	4.2	—	
t_{rr}	Reverse recovery time	I_{SD} = 40A	—	90	—	ns
Q_{rr}	Reverse recovery charge	V_{GS} = −5V	—	550	—	nC
I_{rr}	Reverse recovery current	V_R = 800V di_F/dt = 1000 A/µs	—	13.5	—	A

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM170HRM451AG device.

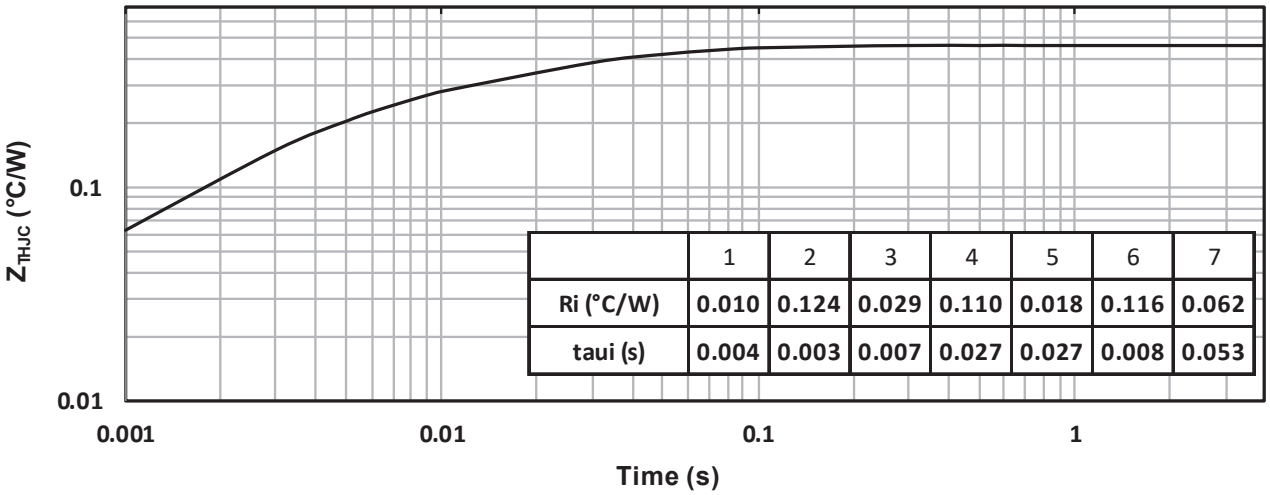
Table 1-9. Thermal and Package Characteristics

Symbol	Characteristic			Min.	Max.	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			4000	—	V
T_J	Operating junction temperature range			−40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			−40	T_{Jmax} −25	
T_{STG}	Storage temperature range			−40	125	
T_C	Operating case temperature			−40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight			—	80	g

1.4 Typical 1700V SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the Q1 and Q4 1700V phase leg SiC MOSFETs.

Figure 1-1. Maximum Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.010	0.124	0.029	0.110	0.018	0.116	0.062
taui (s)	0.004	0.003	0.007	0.027	0.027	0.008	0.053

Figure 1-2. Output Characteristics, T_J = 25 °C

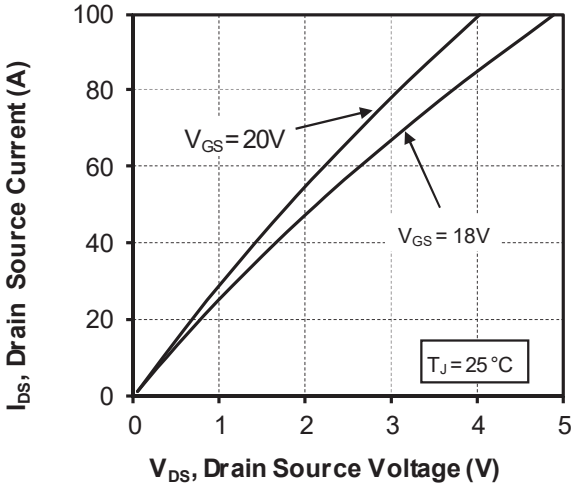


Figure 1-3. Output Characteristics, T_J = 175 °C

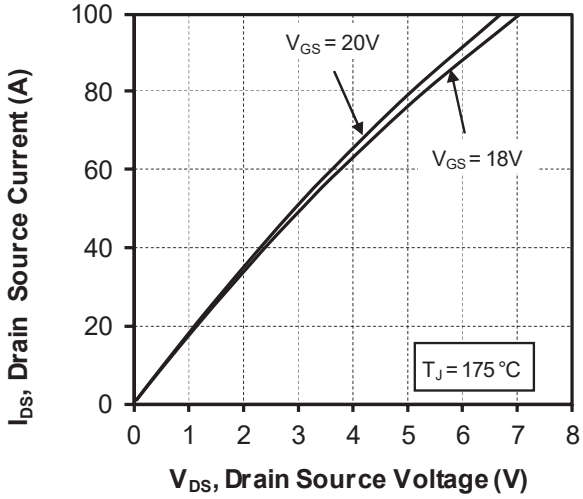


Figure 1-4. Normalized $R_{DS(on)}$ vs. Temperature

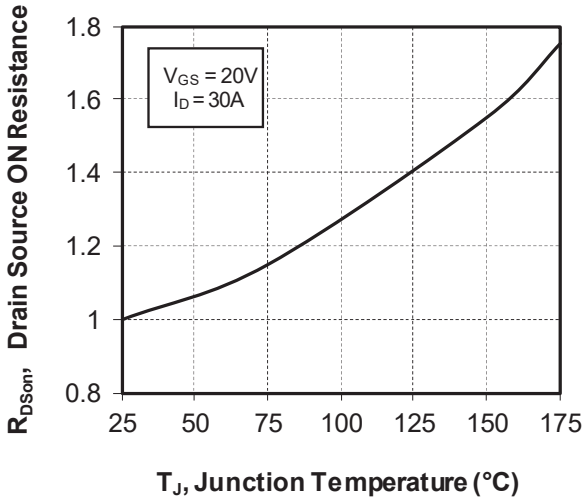


Figure 1-5. Transfer Characteristics

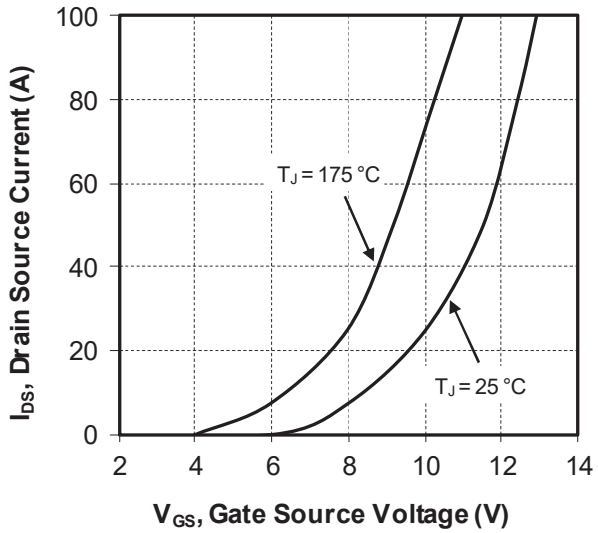


Figure 1-6. Switching Energy vs. Rg

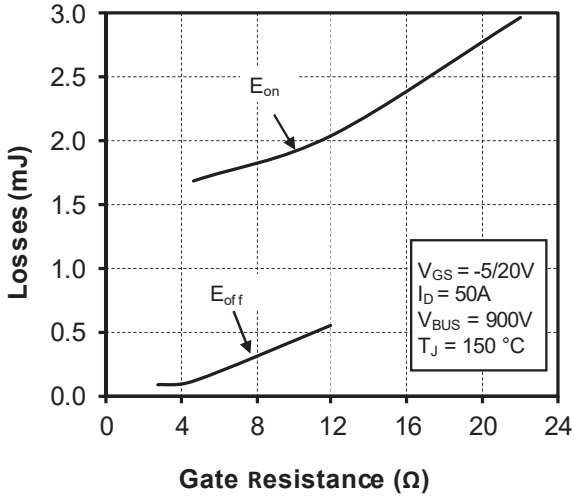


Figure 1-7. Switching Energy vs. Current

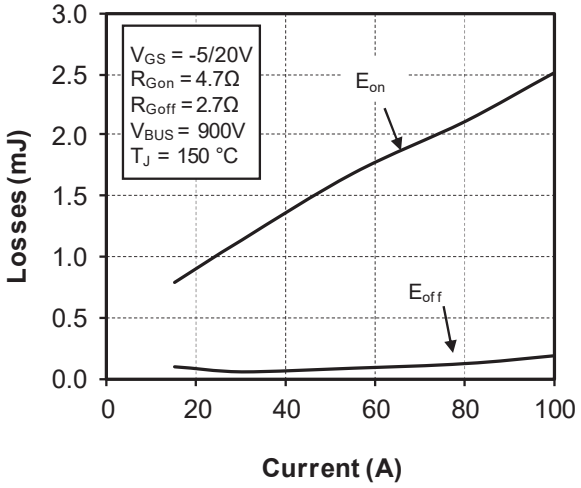


Figure 1-8. Capacitance vs. Drain Source Voltage

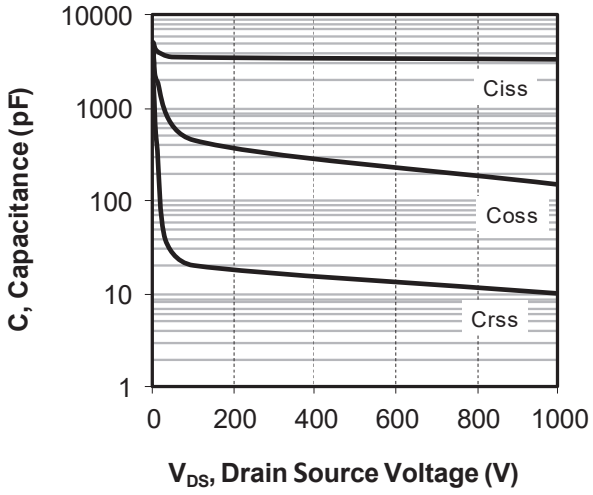


Figure 1-9. Gate Charge vs. Gate Source Voltage

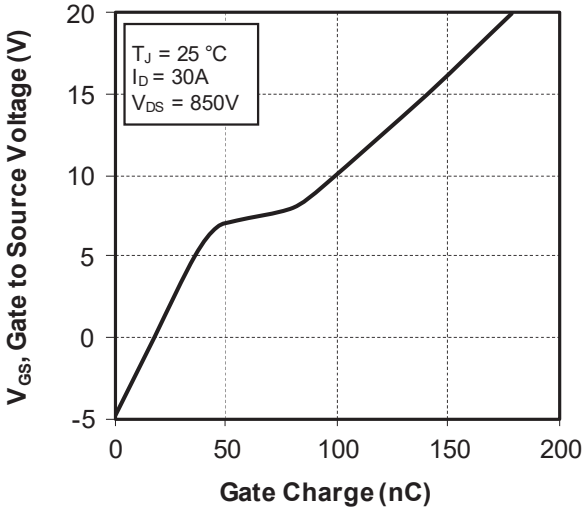


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

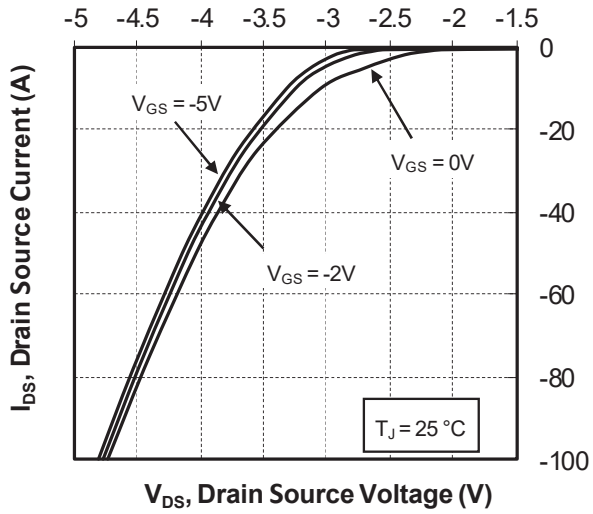


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

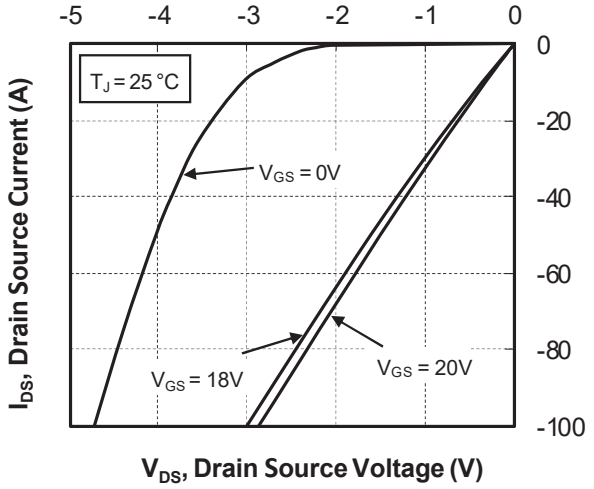


Figure 1-12. Body Diode Characteristics, T_J = 175 °C

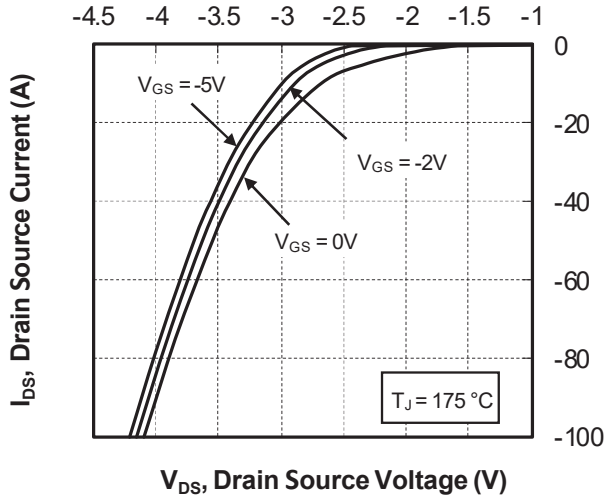


Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C

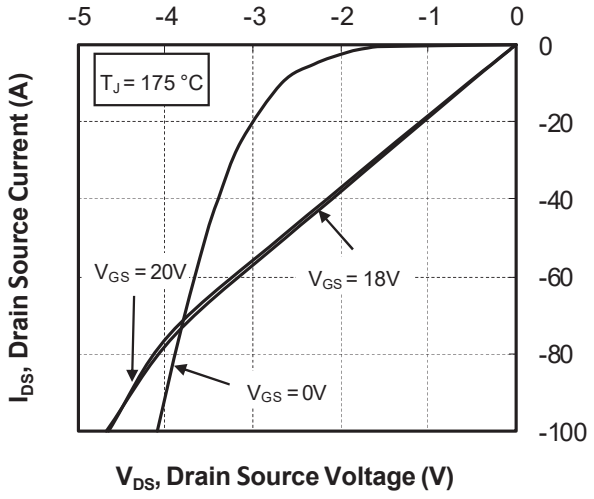
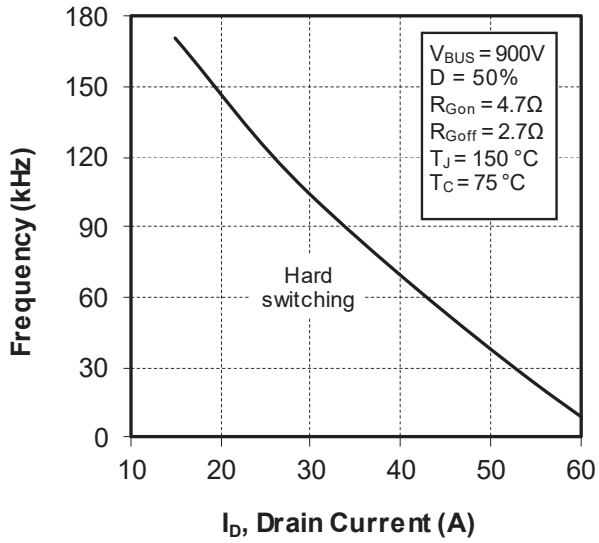


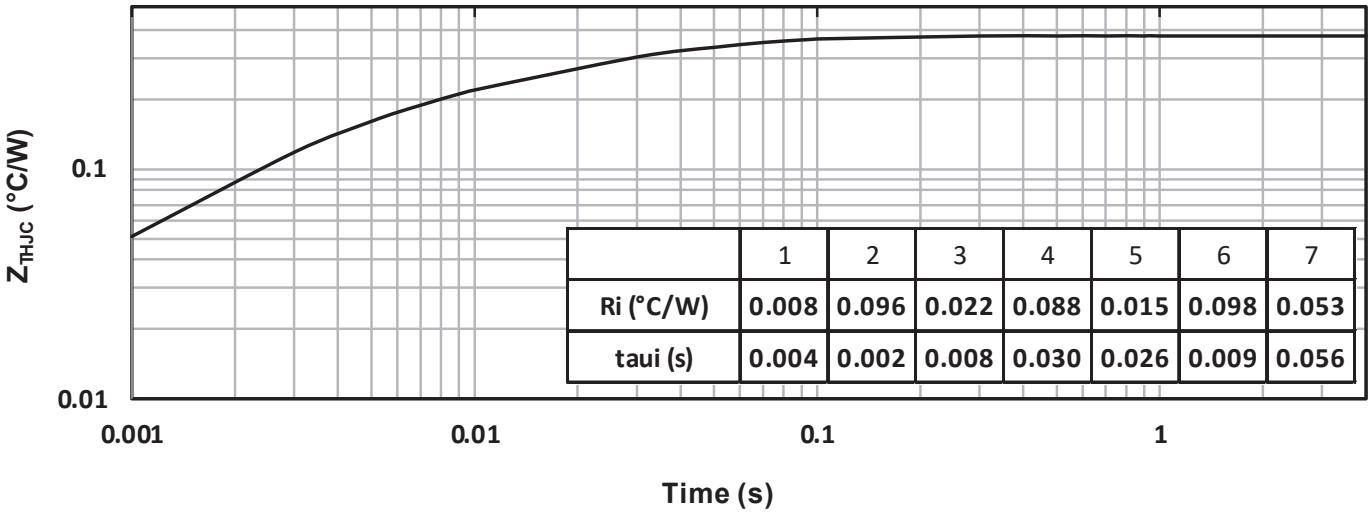
Figure 1-14. Operating Frequency vs. Drain Current



1.5 Typical 1200V SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the Q2 and Q3 1200V dual common source SiC MOSFETs.

Figure 1-15. Maximum Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.008	0.096	0.022	0.088	0.015	0.098	0.053
taui (s)	0.004	0.002	0.008	0.030	0.026	0.009	0.056

Figure 1-16. Output Characteristics, T_J = 25 °C

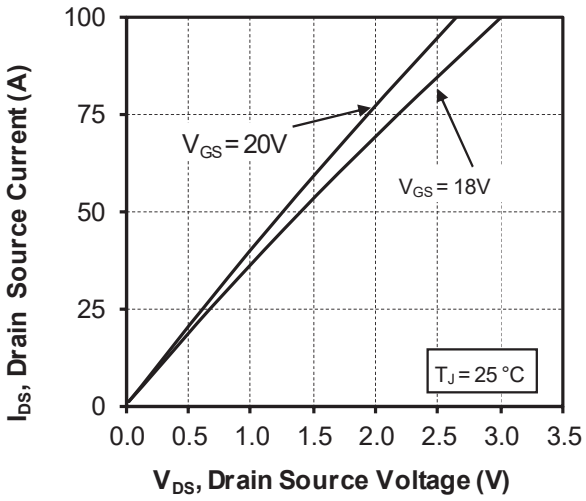


Figure 1-17. Output Characteristics, T_J = 175 °C

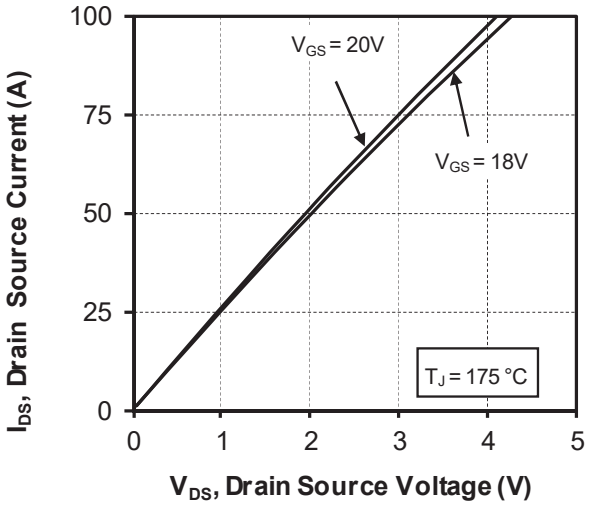


Figure 1-18. Normalized $R_{DS(on)}$ vs. Temperature

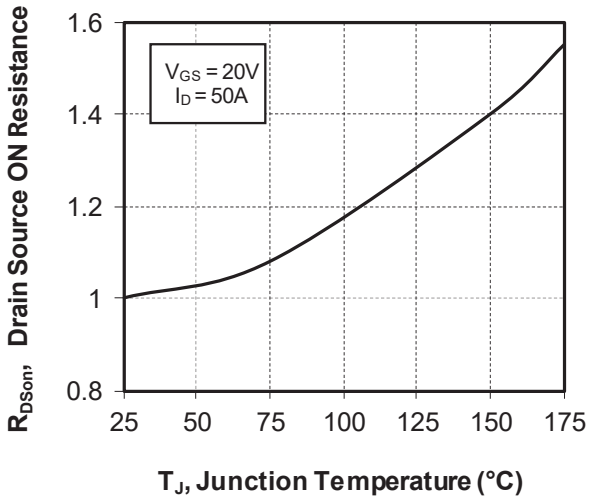


Figure 1-19. Transfer Characteristics

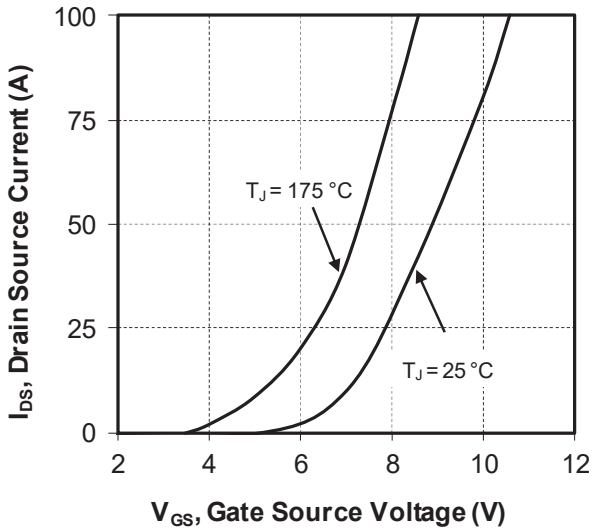


Figure 1-20. Switching Energy vs. Rg

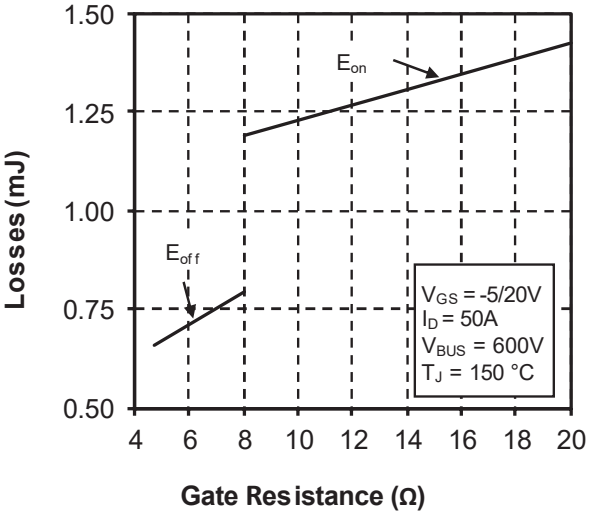


Figure 1-21. Switching Energy vs. Current

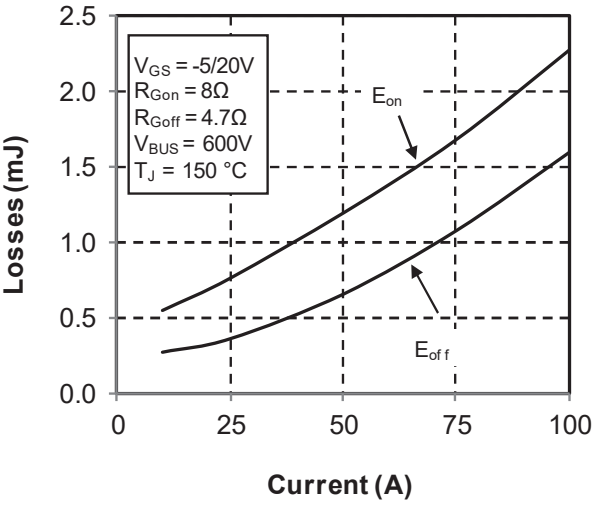


Figure 1-22. Capacitance vs. Drain Source Voltage

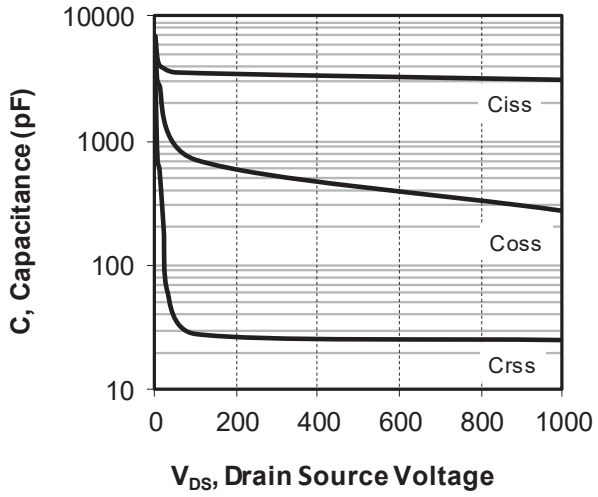


Figure 1-23. Gate Charge vs. Gate Source Voltage

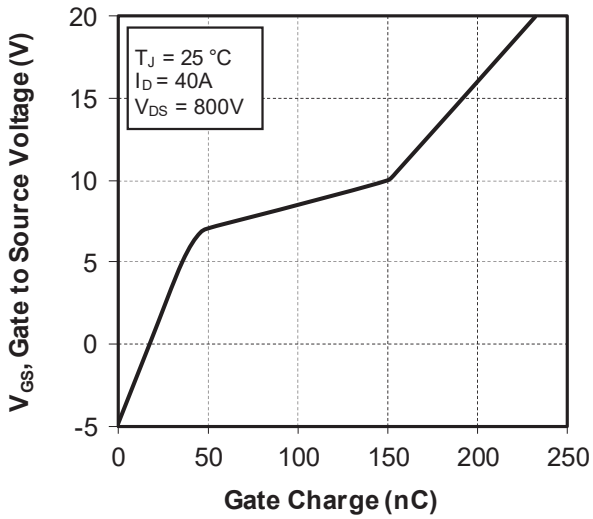


Figure 1-24. Body Diode Characteristics, T_J = 25 °C

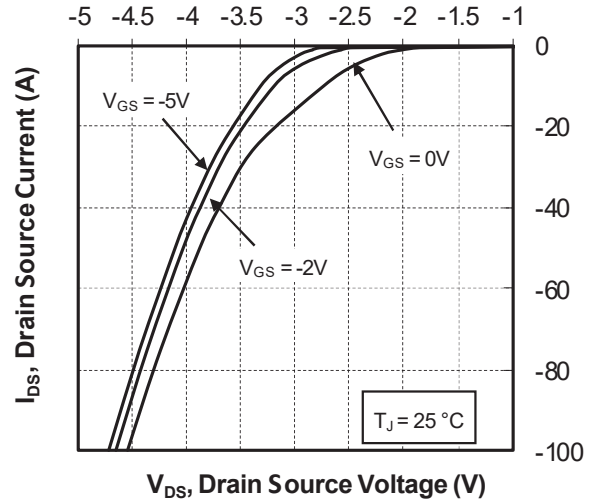


Figure 1-25. 3rd Quadrant Characteristics, T_J = 25 °C

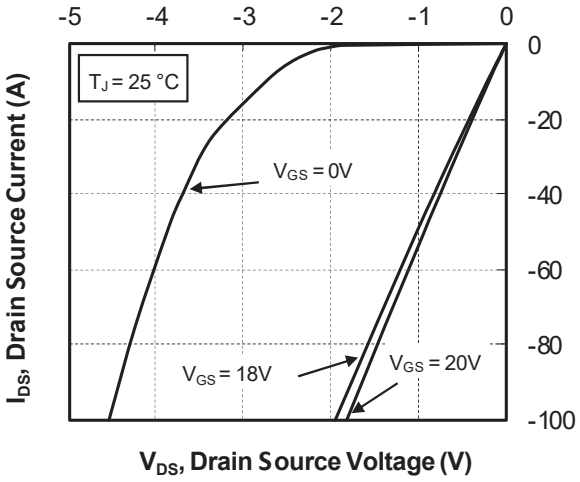


Figure 1-26. Body Diode Characteristics, T_J = 175 °C

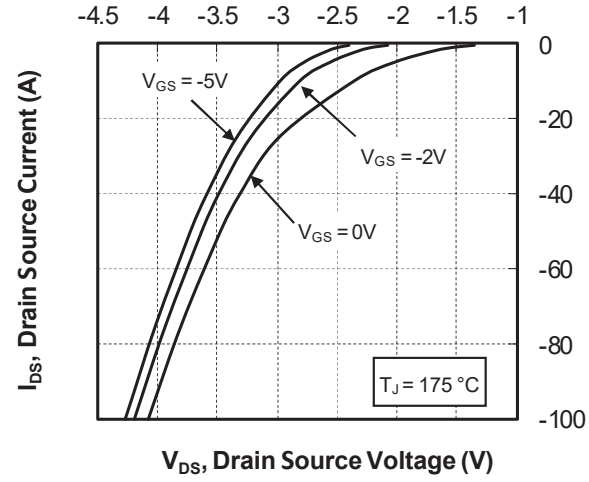


Figure 1-27. 3rd Quadrant Characteristics, T_J = 175 °C

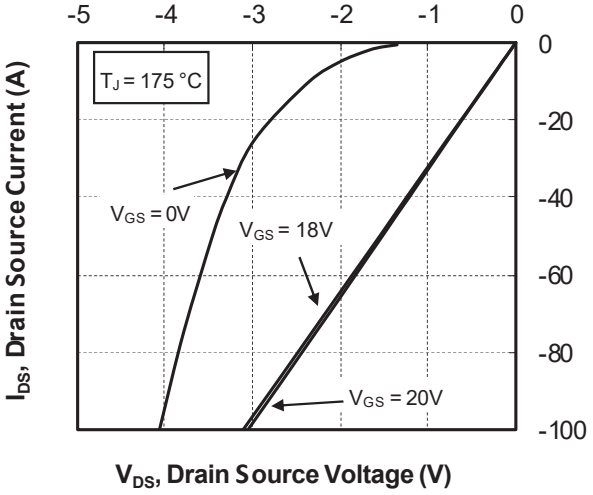
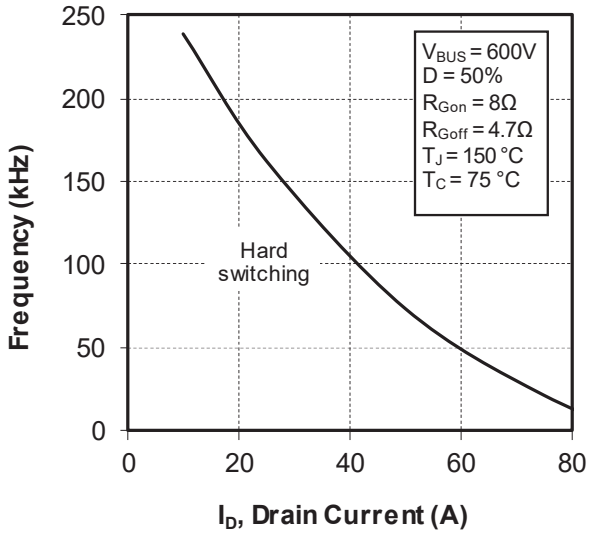


Figure 1-28. Operating Frequency vs. Drain Current



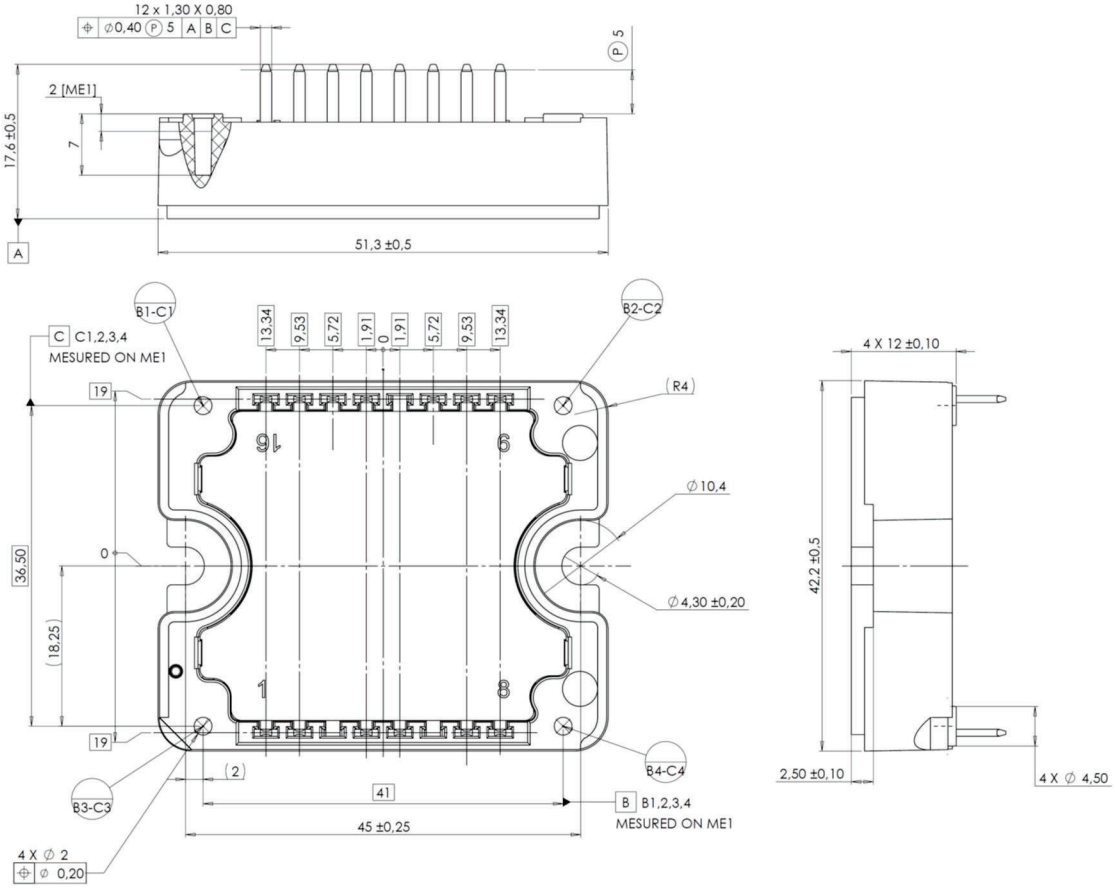
2. Package Specifications

The following section shows the package specification of the MSCSM170HRM451AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM170HRM451AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: For more information, see AN3500—Mounting Instructions for SP1F and SP3F Power Modules.

3. Revision History

Revision	Date	Description
A	02/2023	Initial revision

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